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FDP5N60NZ / FDPF5N60NZ N-Channel UniFETTM II MOSFET 600 V, 4.5 A, 2.0 Ω

Features

- $R_{DS(on)}$ = 1.65 Ω (Typ.) @ V_{GS} = 10 V, I_D = 2.25 A
- Low Gate Charge (Typ. 10 nC)
- Low C_{rss} (Typ. 5 pF)
- 100% Avalanche Tested
- Improved dv/dt Capability
- ESD Improved Capability
- RoHS Compliant

Applications

- LCD / LED / PDP TV
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

Description

UniFETTM II MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on advanced planar stripe and DMOS technology. This advanced MOSFET family has the smallest on-state resistance among the planar MOSFET, and also provides superior switching performance and higher avalanche energy strength. In addition, internal gate-source ESD diode allows UniFET II MOSFET to withstand over 2kV HBM surge stress. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.

D



November 2013

G_{DS} TO-220 G_{DS} TO-220F

MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Parameter			FDP5N60NZ	FDPF5N60NZ	Unit
Drain to Source Voltage		600		V	
Gate to Source Voltage			±	V	
Ducia Quancat	- Continuous (T _C = 25 ^o C)		4.5	4.5*	•
Drain Current	- Continuous (T _C = 100 ^o C)		2.7	2.7*	A
Drain Current	- Pulsed	(Note 1)	18	18*	Α
Single Pulsed Avalanche Energy (Note 2)		175		mJ	
Avalanche Current		(Note 1)	4.5		Α
Repetitive Avalanche Energy		(Note 1)	10		mJ
MOSFET dv/dt			2	20	V/ns
Peak Diode Recovery dv/dt (Note		(Note 3)	10		V/ns
Dower Dissinction	(T _C = 25°C)		100	33	W
Power Dissipation	- Derate above 25°C		0.8	0.27	W/ºC
Operating and Storage Temperature Range		-55 to +150		°C	
Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds 300		00	°C		
	Gate to Source Voltage Drain Current Drain Current Single Pulsed Avalanche En Avalanche Current Repetitive Avalanche Energ MOSFET dv/dt Peak Diode Recovery dv/dt Power Dissipation Operating and Storage Tem	$\begin{tabular}{ c c c } \hline Drain to Source Voltage & \\ \hline Gate to Source Voltage & \\ \hline Gate to Source Voltage & \\ \hline Gate to Source Voltage & \\ \hline Drain Current & \\ \hline - Continuous (T_C = 25^{\circ}C) & \\ \hline - Continuous (T_C = 100^{\circ}C) & \\ \hline - Pulsed & \\ \hline Single Pulsed Avalanche Energy & \\ \hline Avalanche Current & \\ \hline Repetitive Avalanche Energy & \\ \hline Avalanche Current & \\ \hline Repetitive Avalanche Energy & \\ \hline MOSFET dv/dt & \\ \hline Peak Diode Recovery dv/dt & \\ \hline Power Dissipation & \\ \hline (T_C = 25^{\circ}C) & \\ \hline - Derate above 25^{\circ}C & \\ \hline Operating and Storage Temperature Range & \\ \hline \end{tabular}$	$\begin{array}{c} \mbox{Drain to Source Voltage} \\ \hline \mbox{Gate to Source Voltage} \\ \hline \mbox{Gate to Source Voltage} \\ \hline \mbox{Drain Current} & - \mbox{Continuous } (T_{C} = 25^{\circ}\text{C}) \\ \hline \mbox{- Continuous } (T_{C} = 100^{\circ}\text{C}) \\ \hline \mbox{Drain Current} & - \mbox{Pulsed} & (Note 1) \\ \hline \mbox{Single Pulsed Avalanche Energy} & (Note 2) \\ \hline \mbox{Avalanche Current} & (Note 1) \\ \hline \mbox{Repetitive Avalanche Energy} & (Note 1) \\ \hline \mbox{Repetitive Avalanche Energy} & (Note 1) \\ \hline \mbox{MOSFET dv/dt} & \hline \\ \hline \mbox{Peak Diode Recovery dv/dt} & (Note 3) \\ \hline \mbox{Power Dissipation} & \hline \\ \hline \mbox{Cr} = 25^{\circ}\text{C} \\ \hline \mbox{Operating and Storage Temperature Range} \\ \hline \end{array}$	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c } \hline Drain to Source Voltage & 600 \\ \hline Gate to Source Voltage & \pm 25 \\ \hline Gate to Source Voltage & - Continuous (T_C = 25^{\circ}C) & 4.5 & 4.5^{*} \\ \hline - Continuous (T_C = 100^{\circ}C) & 2.7 & 2.7^{*} \\ \hline Drain Current & - Pulsed & (Note 1) & 18 & 18^{*} \\ \hline Single Pulsed Avalanche Energy & (Note 2) & 175 \\ \hline Avalanche Current & (Note 1) & 4.5 \\ \hline Repetitive Avalanche Energy & (Note 1) & 10 \\ \hline MOSFET dv/dt & 20 \\ \hline Peak Diode Recovery dv/dt & (Note 3) & 10 \\ \hline Power Dissipation & \hline (T_C = 25^{\circ}C) & 0.8 & 0.27 \\ \hline Operating and Storage Temperature Range & -55 to +150 \\ \hline \end{array}$

Thermal Characteristics

Symbol	Parameter	FDP5N60NZ	FDPF5N60NZ	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	1.25	3.75	°C/W
R_{\thetaJA}	Thermal Resistance, Junction to Ambient, Max.	62.5	62.5	C/W

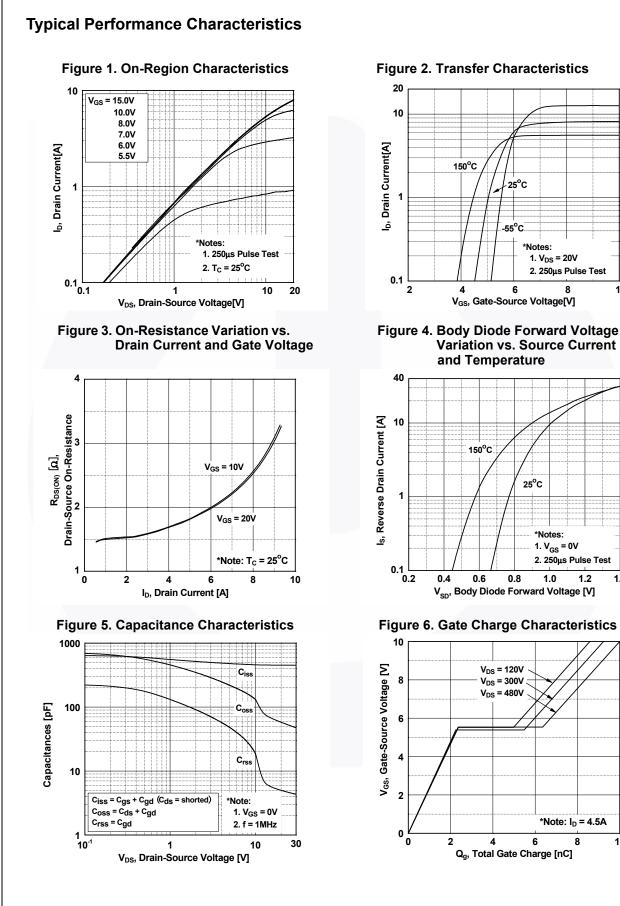
Part Nu	mber	Top Mark	Package	Packing Method	Reel Size	• T	ape Width	Qu	antity	
FDP5N60NZ		FDP5N60NZ	TO-220	Tube	N/A		N/A		50 units	
		TO-220F	O-220F Tube N/A		N/A		50 units			
Electrica	l Chara		Cunless othe	rwise noted						
Symbol		Parameter		Test Condition	s	Min.	Тур.	Max.	Unit	
Off Charac	teristics	•					,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	-		
BV _{DSS}			e la i	= 250 μA, V _{GS} = 0 V		600	-	-	V	
ΔBV_{DSS}	Drain to Source Breakdown Voltage Breakdown Voltage Temperature Coefficient			$I_D = 250 \ \mu$ A, Referenced to 25° C		000				
$/\Delta T_J$						-	0.6	-	V/ºC	
	Zero Gate Voltage Drain Current			_S = 600 V, V _{GS} = 0 V		-	-	1	μA	
DSS	2010 00	Zero Cale Voltage Brain Carrent		V _{DS} = 480 V, T _C = 125 ^o C			-	10	μι	
I _{GSS}	Gate to I	Body Leakage Current	V _G	$_{\rm S}$ = ±25 V, V _{DS} = 0 V		-	-	±10	μA	
On Charac	teristics	;								
V _{GS(th)}	Gate Th	reshold Voltage	V _G	_{iS} = V _{DS} , I _D = 250 μA		3.0	-	5.0	V	
R _{DS(on)}	Static Dr	ain to Source On Resistar	ice V _G	_{iS} = 10 V, I _D = 2.25 A		-	1.65	2.0	Ω	
9 _{FS}	Forward	Transconductance	VD	_S = 20 V, I _D = 2.25 A		-	5	-	S	
Dynamic C	haracte	ristics								
C _{iss}	Input Ca	pacitance				-	450	600	pF	
C _{oss}	Output C	apacitance		V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		-	50	65	pF	
C _{rss}	Reverse	Transfer Capacitance	T =			-	5	7.5	pF	
Q _g	Total Gat	te Charge at 10V	Vn	$V_{DS} = 480 \text{ V}, \text{ I}_{D} = 4.5 \text{ A},$ $V_{GS} = 10 \text{ V} $ (Note 4)		-	10	13	nC	
Q _{gs}	Gate to S	Source Gate Charge				-	2.5	-	nC	
Q _{gd}	Gate to I	Drain "Miller" Charge				-	4	-	nC	
Switching	Charact	eristics								
t _{d(on)}		Delay Time	V-	- = 300 V I_ = 4.5 A		-	15	40	ns	
t _r		Turn-On Rise Time		$V_{DD} = 300 \text{ V}, \text{ I}_{D} = 4.5 \text{ A},$ $V_{GS} = 10 \text{ V}, \text{ R}_{G} = 25 \Omega$		-	20	50	ns	
t _{d(off)}	Turn-Off	Delay Time				-	35	80	ns	
t _f	Turn-Off	Fall Time			(Note 4)		20	50	ns	
Drain-Sou	rce Diod	e Characteristics					_11		-1	
I _S	1	n Continuous Drain to Sou	rce Diode Fo	rward Current			_	4.5	Α	
I _{SM}		n Pulsed Drain to Source [-	_	18	A	
V _{SD}	Drain to Source Diode Forward Voltage			$V_{GS} = 0 V, I_{SD} = 4.5 A$		-	-	1.4	V	
t _{rr}		Recovery Time		$V_{GS} = 0 V, I_{SD} = 4.5 A,$ dI _E /dt = 100 A/µs		-	230	-	ns	
Q _{rr}		Recovery Charge				-	0.9	-	μC	
Notes: 1. Repetitive rating 2. L = 17.3 mH, I _A ; 3. I _{SD} ≤ 4.5 A, di/d	g: pulse-width li _S = 4.5 A, V _{DD} t ≤ 200 A/μs, V	imited by maximum junction tempe = 50 V, R _G = 25 Ω , starting T _J = 25 $^{'}_{DD} \leq BV_{DSS}$, starting T _J = 25°C. rating temperature typical characte	°C.					6	2	

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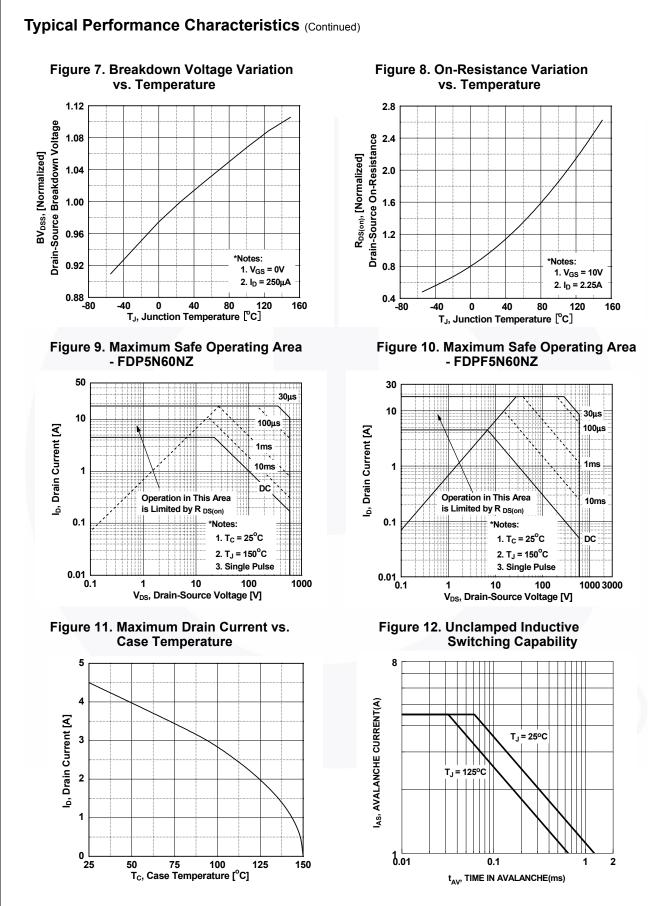
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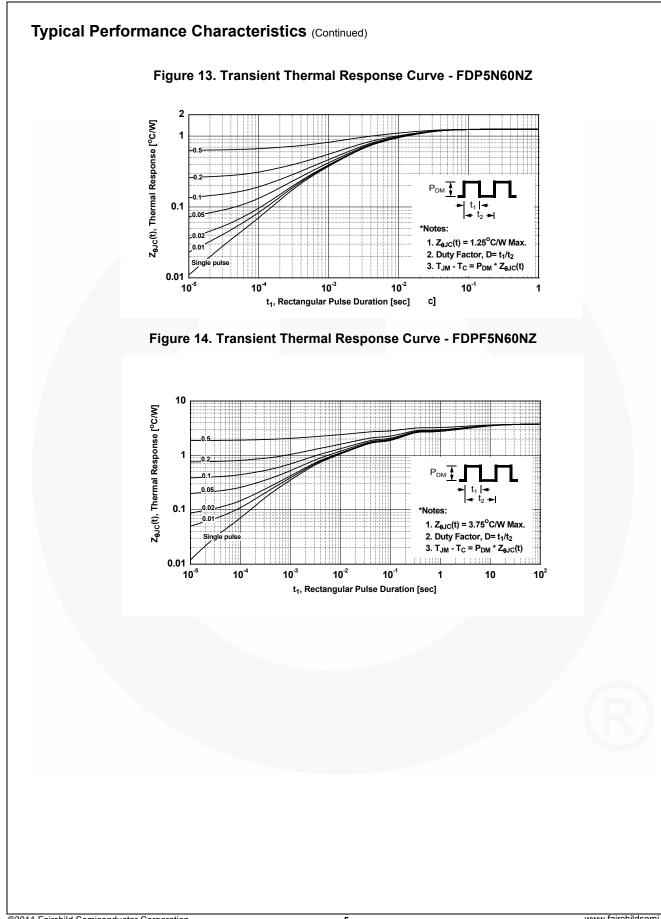


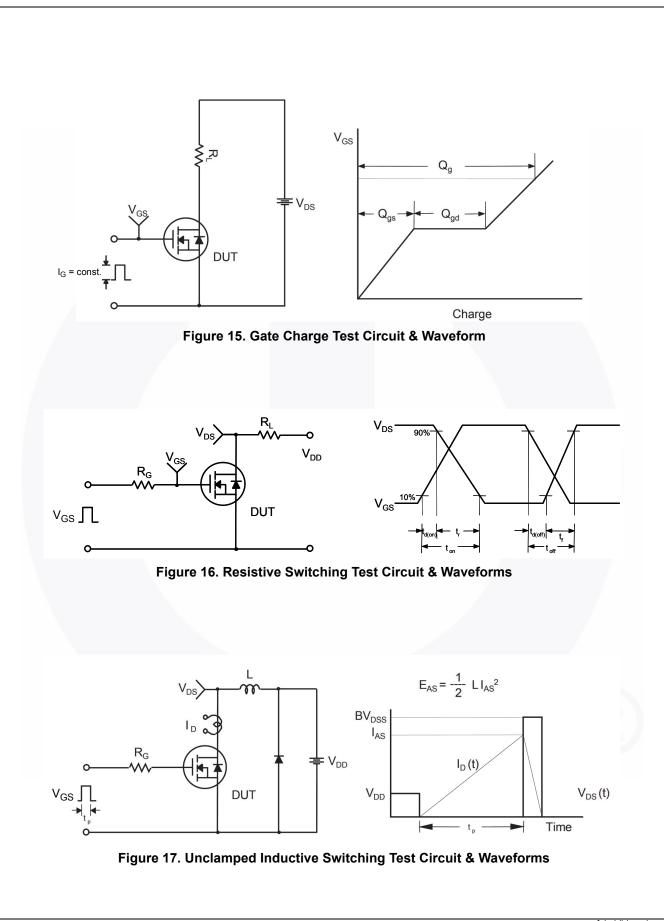
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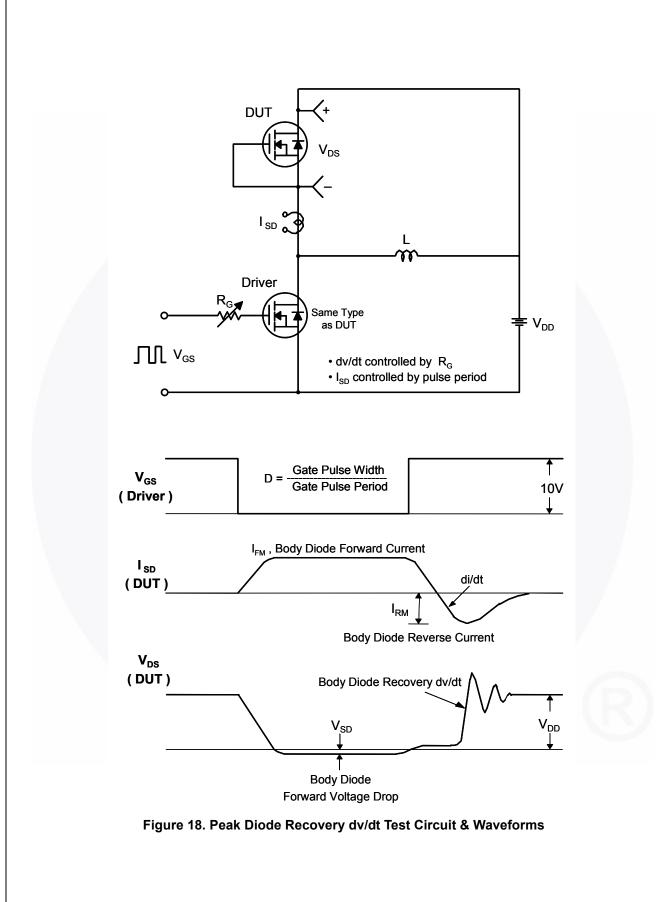


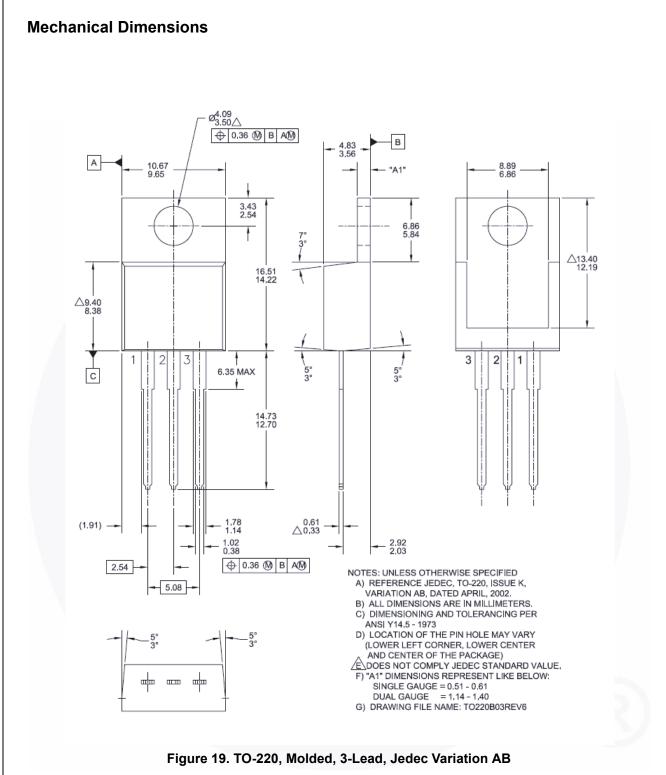
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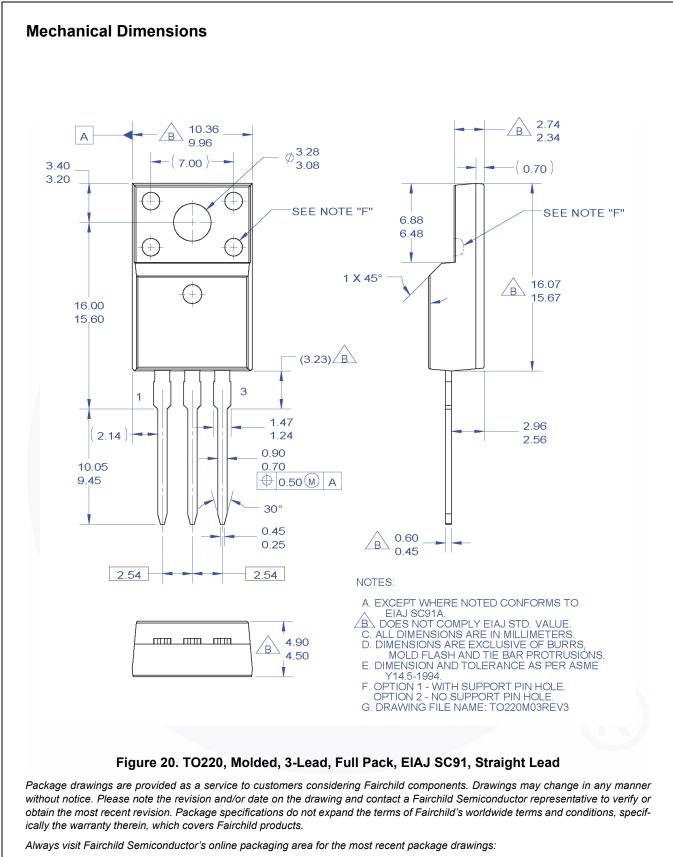




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N-Channel UniFETTM II MOSFET

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